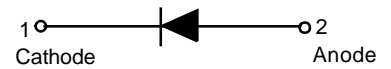
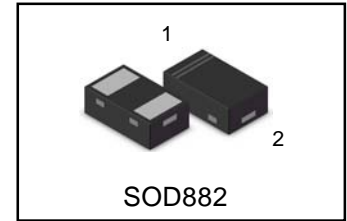


# LBAS16BST5G

## Switching Diode

### 1. FEATURES

- We declare that the material of product compliance with RoHS requirements and Halogen Free.
- Small plastic SMD package.
- Continuous reverse voltage: max. 75 V.
- High-speed switching in hybrid thick and thin-film circuits.



### 2. DEVICE MARKING AND RESISTOR VALUES

Device	Marking	Shipping
LBAS16BST1G	3(Note 1)	5000/Tape&Reel
LBAS16BST3G	3(Note 1)	8000/Tape&Reel
LBAS16BST5G	3(Note 1)	10000/Tape&Reel

1. Rotated 90°

### 3. MAXIMUM RATINGS(Ta = 25°C)

Parameter	Symbol	Limits	Unit
Continuous reverse voltage	VR	75	V
Peak Forward Current	IF	200	mA
Peak Forward Surge Current	IFSM	500	mA

### 4. THERMAL CHARACTERISTICS

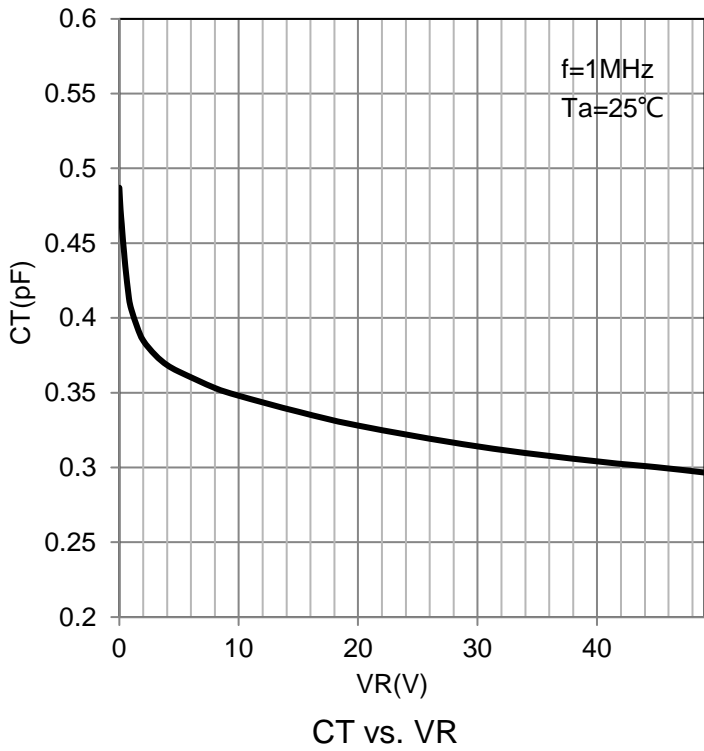
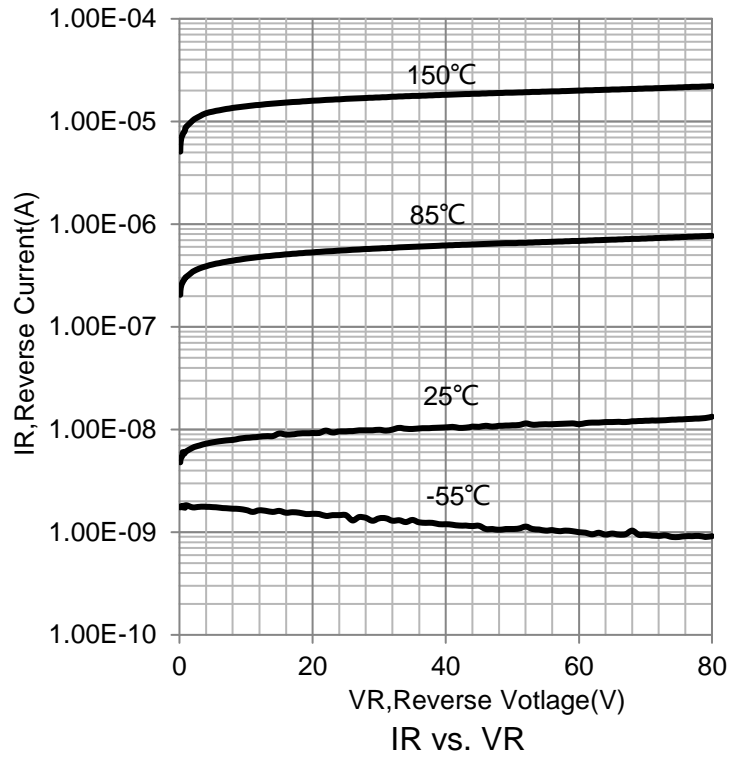
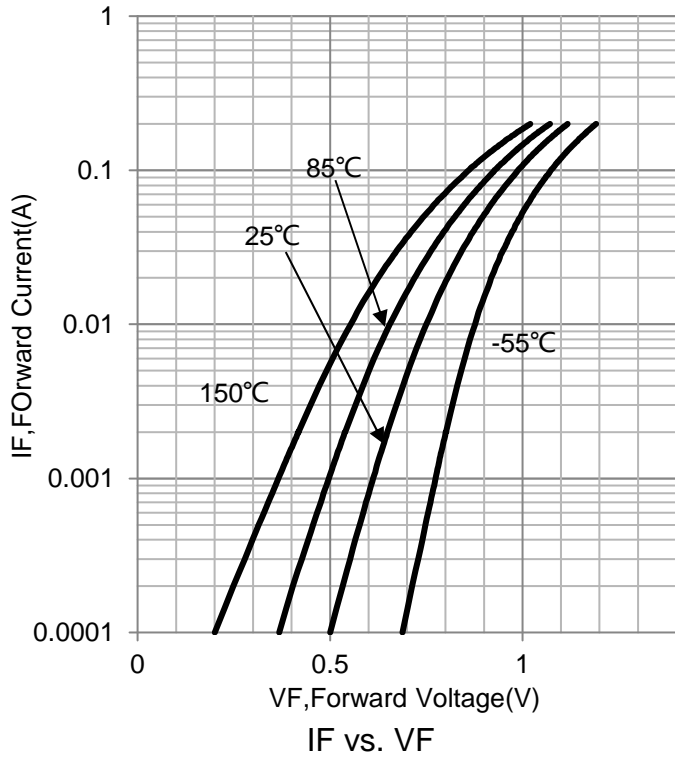
Parameter	Symbol	Limits	Unit
Total Device Dissipation FR- 5 Board, (Note 2) TA = 25°C	PD	200	mW
Derate above 25°C		1.57	mW/°C
Thermal resistance from junction to ambient	RθJA	635	°C/W
Junction and Storage Temperature	TJ , Tstg	-55~+150	°C

2.FR-4 Minimum Pad

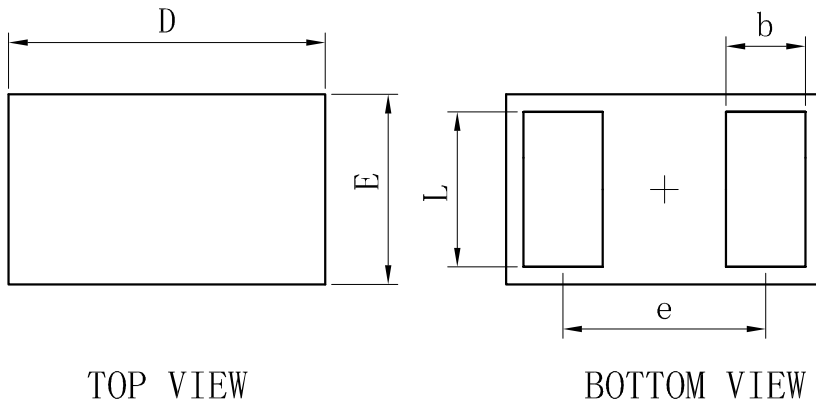
**5. ELECTRICAL CHARACTERISTICS (Ta= 25°C)**

CHARACTERISTICS	Symbol	Min	Max	Unit
Reverse Voltage Leakage Current (VR=75V) (VR=75V, TJ = 150°C) (VR=25V, TJ = 150°C)	IR	- - -	1 50 30	μA
Reverse Breakdown Voltage (IBR = 100 μA)	VBR	75	-	V
Forward voltage (IF =1mA) (IF =10mA) (IF =50mA) (IF =150mA)	VF	- - - -	715 855 1000 1250	mV
Diode capacitance (f=1MHz, VR =0)	Cd	-	2	pF
Reverse Recovery Time (IF = IR = 10mA, RL = 50 Ω)	Trr	-	4	nS
Forward Recovery Voltage (IF = 10 mA, tr = 20 ns)	VFR	-	1.75	V
Stored Charge (IF = 10 mA, VR = 5.0 V, RL = 500 Ω)	QS	-	45	pC

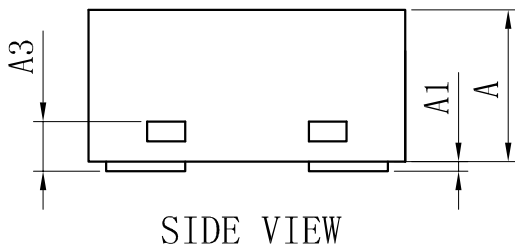
**6.ELECTRICAL CHARACTERISTICS CURVES**



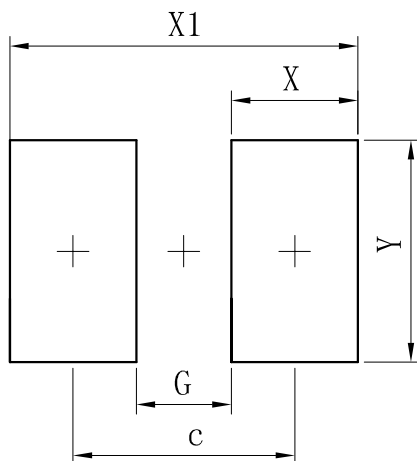
### 7. OUTLINE AND DIMENSIONS



SOD882			
Dim	Min	Typ.	Max
D	0.95	1.00	1.05
E	0.55	0.60	0.65
e	-	0.64	-
L	0.44	0.49	0.54
b	0.20	0.25	0.30
A	0.43	0.48	0.53
A1	0	-	0.05
A3	0.127REF.		
All Dimensions in mm			



### 8. SOLDERING FOOTPRINT



Dimensions	(mm)
c	0.70
G	0.30
X	0.40
X1	1.10
Y	0.70